









MAX3223E SLLS707B - JANUARY 2006 - REVISED DECEMBER 2023

# 3-V to 5.5-V Multichannel RS-232 Line Driver and Receiver with ±15-kV ESD **Protection**

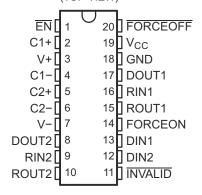
#### 1 Features

- ESD Protection for RS-232 bus pins
  - ±15-kV Human-body model (HBM)
  - ±8-kV IEC61000-4-2, Contact discharge
  - ±15-kV IEC61000-4-2, Air-gap discharge
- Meets or exceeds the requirements of TIA/ EIA-232-F and ITU v.28 standards
- Operates with 3-V to 5.5-V V<sub>CC</sub> supply
- Operates up to 500 kbit/s
- Two drivers and two receivers
- Low standby current: 1 µA typical
- External capacitors: 4 × 0.1 µF
- Accepts 5-V logic input With 3.3-V supply
- Alternative high-speed pin-compatible device (1 Mbit/s) for SNx5C3223E

# 2 Applications

- **Battery-powered systems**
- **PDAs**
- **Notebooks**
- Laptops
- Palmtop PCs
- Hand-held equipment

DB, DW, OR PW PACKAGE (TOP VIEW)



## 3 Description

The MAX3223E consists of two line drivers, two line receivers, and a dual charge-pump circuit with ±15-kV ESD protection pin to pin (serial-port connection pins, including GND). The device meets the requirements of TIA/EIA-232-F and provides the electrical interface between an asynchronous communication controller and the serial-port connector. The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. The device operates at typical data signaling rates up to 500 kbit/s and a maximum of 30-V/µs driver output slew rate.

Flexible control options for power management are available when the serial port is inactive. The autopowerdown feature functions when FORCEON is low and FORCEOFF is high. During this mode of operation, if the device does not sense a valid RS-232 signal, the driver outputs are disabled. If FORCEOFF is set low and EN is high, both drivers and receivers are shut off, and the supply current is reduced to 1 mA. Disconnecting the serial port or turning off the peripheral drivers causes auto-powerdown to occur. Auto-powerdown can be disabled when FORCEON and FORCEOFF are high. With auto-powerdown enabled, the device is activated automatically when a valid signal is applied to any receiver input. The INVALID output is used to notify the user if an RS-232 signal is present at any receiver input. INVALID is high (valid data) if any receiver input voltage is greater than 2.7 V or less than -2.7 V, or has been between -0.3 V and 0.3 V for less than 30 μs. INVALID is low (invalid data) if the receiver input voltage is between –0.3 V and 0.3 V for more than 30 μs. Refer to Figure 5-4 for receiver input levels.

#### **Package Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	PACKAGE SIZE <sup>(2)</sup>			
	SOIC (DW, 20)	12.8 mm × 10.3 mm			
MAX3223E	SSOP (DB, 20)	7.2 mm × 7.8 mm			
	TSSOP (PW, 20)	6.5 mm x 6.4 mm			

- For more information, see Section 10.
- The package size (length × width) is a nominal value and includes pins, where applicable.



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# 4 Specifications

## 4.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage range		-0.3	6	V
V+	Positive-output supply voltage range <sup>(2)</sup>		-0.3	7	V
V-	Negative-output supply voltage range <sup>(2)</sup>		0.3	-7	V
V+ - V-	Supply voltage difference <sup>(2)</sup>			13	V
	Input voltage range	Driver ( FORCEOFF, FORCEON, EN)	-0.3	6	\/
V <sub>I</sub>		Receiver	-25	25	V
	Out	Driver	-13.2	13.2	.,
Vo	Output voltage range	Receiver ( INVALID)	-0.3	V <sub>CC</sub> + 0.3	V
T <sub>J</sub>	Operating virtual junction temperature			150	°C
T <sub>stg</sub>	Storage temperature range		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### 4.2 Recommended Operating Conditions

See Figure 7-1, and (1)

				MIN	NOM	MAX	UNIT
	Supply voltage	V <sub>CC</sub> = 3.3 V	3	3.3	3.6	V	
	Supply voltage		V <sub>CC</sub> = 5 V	4.5	5	5.5	V
V <sub>IH</sub>	Driver and control high-level input voltage	DIN, EN, FORCEOFF, FORCEON	V <sub>CC</sub> = 3.3 V	2			V
		DIN, EN, FORGEON	V <sub>CC</sub> = 5 V	2.4			V
V <sub>IL</sub>	Driver and control low-level input voltage	DIN, EN, FORCEOFF, FORCEON	DIN, EN, FORCEOFF, FORCEON			8.0	V
.,	Driver and control input voltage	DIN, EN, FORCEOFF, FORCEON		0		5.5	V
VI	Receiver input voltage			-25	,	25	V
_	Operating free-air temperature	On anothing for a girl to man another.		0		70	°C
T <sub>A</sub>	Operating nee-all temperature		MAX3223EI	<del>-4</del> 0		85	C

<sup>(1)</sup> Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V ± 0.5 V.

#### 4.3 ESD Ratings

	- itatii.go				
				VALUE	UNIT
		Human-body model (HBM), per ANSI/	All pins except RIN1, RIN2, DOUT1 and DOUT2 pins	±3000	
V <sub>(ESD)</sub>	Electrostatic ESDA/JEDEC JS-001 <sup>(1)</sup> RIN1 RIN2 DOLIT1 and DOLIT2 pins to	±15000	V		
		Charged device model (CDM), per ANSI/ ESDA/JEDEC JS-002 <sup>(2)</sup>	All pins	±1500	

<sup>(1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

<sup>(2)</sup> All voltages are with respect to network GND.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



# 4.4 ESD Ratings - IEC Specifications

				VALUE	UNIT
	V Floatroctatio discharge	IEC 61000-4-2 Contact Discharge <sup>(1)</sup>	±8000	\/	
V (ESD)	(ESD)	Electrostatic discharge	IEC 61000-4-2 Air-gap Discharge <sup>(1)</sup>	±15,000	V

(1) A minimum of 1-µF capacitor between V<sub>CC</sub> and GND is required to meet the specified IEC 61000-4-2 rating.

#### 4.5 Thermal Information

	THERMAL METRIC <sup>(1)</sup>	DB (SOIC)	DW (SOIC)	PW (TSSOP)	UNIT
	THERMAL WETRIO		20 PINS	20 PINS	UNII
$R_{\theta JA}$	Junction-to-ambient thermal resistance	87.2	76.8	89.7	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	41.1	39.6	29.0	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	43.3	41.5	41.9	°C/W
ΨЈТ	Junction-to-top characterization parameter	9.2	12.6	1.9	°C/W
ΨЈВ	Junction-to-board characterization parameter	42.7	40.9	41.3	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

#### 4.6 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5-5) and <sup>(1)</sup>

	PARA	METER	TEST CONDITIONS	MIN	TYP <sup>(2)</sup>	MAX	UNIT
I <sub>1</sub>	Input leakage current	EN, FORCEOFF, FORCEON			±0.01	±1	μΑ
		Auto-powerdown disabled	$V_{CC}$ = 3.3 V or 5 V, $T_A$ = 25°C, No load, FORCEOFF and FORCEON at $V_{CC}$		0.3	1.3	mA
loc	Supply current  No load, FORCE Auto-powerdown enabled GND,	No load, FORCEOFF at GND		1	10		
Icc		Auto-powerdown enabled	No load, FORCEOFF at V <sub>CC</sub> , FORCEON at GND, All RIN are open or grounded		1	10	μΑ

- (1) Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V ± 0.5 V.
- (2) All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25 ^{\circ}\text{C}$ .

#### 4.7 Driver Section

#### 4.7.1 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5-5) and <sup>(1)</sup>

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(2)</sup>	MAX	UNIT
V <sub>OH</sub>	High-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND	5	5.4		V
V <sub>OL</sub>	Low-level output voltage	DOUT at $R_L = 3 \text{ k}\Omega$ to GND	-5	-5.4		V
I <sub>IH</sub>	High-level input current	$V_I = V_{CC}$		±0.01	±1	μΑ
I <sub>IL</sub>	Low-level input current	V <sub>I</sub> at GND		±0.01	±1	μA
Ios	Short-circuit output current <sup>(3)</sup>	V <sub>CC</sub> = 3.6 V, V <sub>O</sub> = 0 V		±35	±60	mA
ios		$V_{CC} = 5.5 \text{ V}, V_{O} = 0 \text{ V}$		100	100	ША
r <sub>o</sub>	Output resistance	$V_{CC}$ , V+, and V- = 0 V, $V_{O}$ = ±2 V	300	10M		Ω
	Output lookage current	$\overline{\text{FORCEOFF}}$ = GND, $V_{\text{CC}}$ = 3 V to 3.6 V, $V_{\text{O}}$ = ±12 V			±25	μA
l <sub>OZ</sub>	Output leakage current	$\overline{\text{FORCEOFF}}$ = GND, $V_{\text{CC}}$ = 4.5 V to 5.5 V, $V_{\text{O}}$ = ±12 V			±25	μА

- (1) Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.
- (2) All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.

(3) Short-circuit durations should be controlled to prevent exceeding the device absolute power dissipation ratings, and not more than one output should be shorted at a time.

#### 4.7.2 Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5-5) and <sup>(1)</sup>

PARAMETER TEST CONDITIONS		MIN	TYP <sup>(2)</sup>	MAX	UNIT		
	Maximum data rate	C <sub>L</sub> = 1000 pF, One DOUT switching,	$R_L = 3 k\Omega$ , See Figure 5-1	250	500		kbit/s
t <sub>sk(p)</sub>	Pulse skew <sup>(3)</sup>	C <sub>L</sub> = 150 pF to 2500 pF, See Figure 5-2	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$		100		ns
SD/tr)	Slew rate, transition region	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$	C <sub>L</sub> = 150 pF to 1000 pF	6		30	V/µs
SR(tr)	(See Figure 5-1)	.,	C <sub>L</sub> = 150 pF to 2500 pF	4		30	v/µS

- (1) Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.
- (2) All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.
- (3) Pulse skew is defined as |t<sub>PLH</sub> t<sub>PHL</sub>| of each channel of the same device.

#### 4.7.3 ESD Protection

		TYP	UNIT
	Human-Body Model (HBM)	±15	
Driver outputs (DOUTx)	IEC61000-4-2, Air-Gap Discharge	±15	kV
	IEC61000-4-2, Contact Discharge	±8	

#### 4.8 Receiver Section

#### 4.8.1 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 7-1) and <sup>(1)</sup>

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(2)</sup>	MAX	UNIT
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -1 mA	V <sub>CC</sub> - 0.6	V <sub>CC</sub> - 0.1		V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 1.6 mA			0.4	V
V <sub>IT+</sub>	Positive-going input threshold voltage	V <sub>CC</sub> = 3.3 V		1.6	2.4	V
VIT+		V <sub>CC</sub> = 5 V		1.9	2.4	v
V	Negative going input threshold voltage	V <sub>CC</sub> = 3.3 V	0.6	1.1		V
V <sub>IT</sub>	Negative-going input threshold voltage	V <sub>CC</sub> = 5 V	0.6	1.4		v
V <sub>hys</sub>	Input hysteresis (V <sub>IT+</sub> - V <sub>IT-</sub> )			0.5		V
I <sub>OZ</sub>	Output leakage current	EN = V <sub>CC</sub>		±0.05		μΑ
rį	Input resistance	V <sub>I</sub> = ±3 V to ±25 V	3	5		kΩ

- (1) Test conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.
- (2) All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.

#### 4.8.2 Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (1)

	PARAMETER	TEST CONDITIONS	TYP <sup>(2)</sup>	UNIT
t <sub>PLH</sub>	Propagation delay time, low- to high-level output	C <sub>L</sub> = 150 pF, See Figure 5-3	150	ns
t <sub>PHL</sub>	Propagation delay time, high- to low-level output	C <sub>L</sub> = 150 pF, See Figure 5-3	150	ns
t <sub>en</sub>	Output enable time	$C_L$ = 150 pF, $R_L$ = 3 k $\Omega$ , See Figure 5-4	200	ns
t <sub>dis</sub>	Output disable time	$C_L$ = 150 pF, $R_L$ = 3 k $\Omega$ , See Figure 5-4	200	ns
t <sub>sk(p)</sub>	Pulse skew <sup>(3)</sup>	See Figure 5-3	50	ns

(1) Test conditions are C1–C4 = 0.1  $\mu$ F at  $V_{CC}$  = 3.3 V ± 0.3 V; C1 = 0.047  $\mu$ F, C2–C4 = 0.33  $\mu$ F at  $V_{CC}$  = 5 V ± 0.5 V.



- (2) All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C. (3) Pulse skew is defined as  $|t_{PLH} t_{PHL}|$  of each channel of the same device.

## 4.8.3 ESD Protection

		TYP	UNIT
	Human-Body Model (HBM)	±15	
Receiver inputs (RINx)	IEC61000-4-2, Air-Gap Discharge	±15	kV
	IEC61000-4-2, Contact Discharge	±8	

#### 4.9 Auto-Powerdown Section

#### 4.9.1 Electrical Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5-5)

	PARAMETER	TEST (	CONDITIONS	MIN	MAX	UNIT
V <sub>T+(valid)</sub>	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	FORCEOFF = V <sub>CC</sub>		2.7	V
V <sub>T(valid)</sub>	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND,	FORCEOFF = V <sub>CC</sub>	-2.7		V
V <sub>T(invalid)</sub>	Receiver input threshold for INVALID low-level output voltage	FORCEON = GND,	FORCEOFF = V <sub>CC</sub>	-0.3	0.3	V
V <sub>OH</sub>	INVALID high-level output voltage	I <sub>OH</sub> = 1 mA, FORCEOFF = V <sub>CC</sub>	FORCEON = GND,	V <sub>CC</sub> - 0.6		V
V <sub>OL</sub>	INVALID low-level output voltage	I <sub>OL</sub> = 1.6 mA, FORCEOFF = V <sub>CC</sub>	FORCEON = GND,		0.4	V

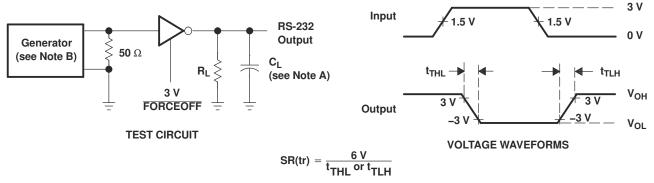
## 4.9.2 Switching Characteristics

over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5-5)

	PARAMETER	TYP <sup>(1)</sup>	UNIT
t <sub>valid</sub>	Propagation delay time, low- to high-level output	1	μs
t <sub>invalid</sub>	Propagation delay time, high- to low-level output	30	μs
t <sub>en</sub>	Supply enable time	100	μs

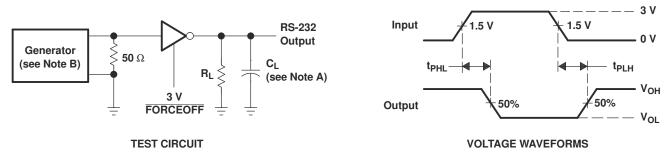
(1) All typical values are at  $V_{CC}$  = 3.3 V or  $V_{CC}$  = 5 V, and  $T_A$  = 25°C.

#### **5 Parameter Measurement Information**



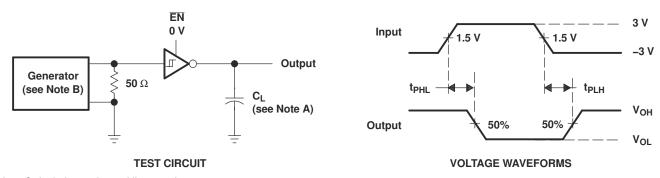
- A. C<sub>L</sub> includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_0 = 50 \Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

Figure 5-1. Driver Slew Rate



- C<sub>L</sub> includes probe and jig capacitance.
- B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_0$  = 50  $\Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

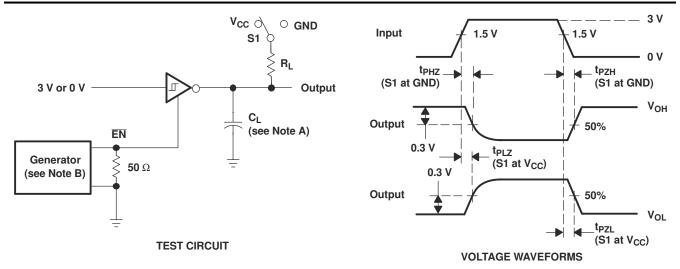
Figure 5-2. Driver Pulse Skew



- C<sub>L</sub> includes probe and jig capacitance.
- B. The pulse generator has the following characteristics:  $Z_0$  = 50  $\Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

Figure 5-3. Receiver Propagation Delay Times





- A. C<sub>L</sub> includes probe and jig capacitance.
- B. The pulse generator has the following characteristics:  $Z_0$  = 50  $\Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

Figure 5-4. Receiver Enable and Disable Times

Valid RS-232 Level, INVALID High

drivers

and

† Auto-powerdown disables

reduces supply current to 1 μA

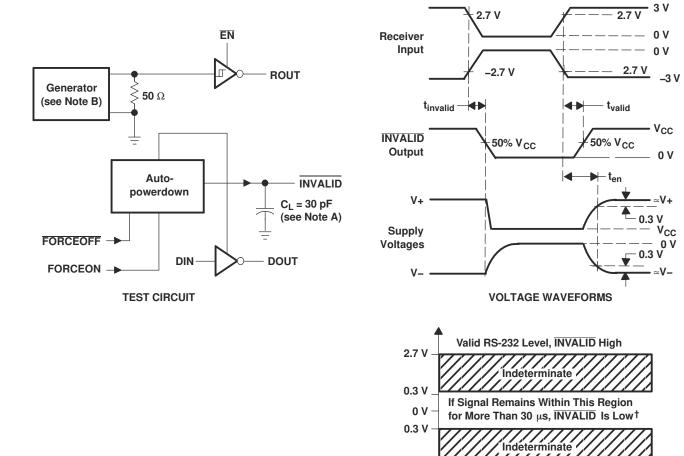


Figure 5-5. INVALID Propagation Delay Times and Supply Enabling Time

2.7 V

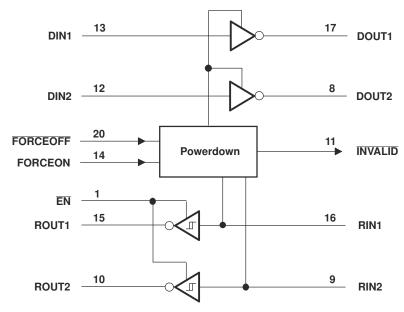
A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 250 kbit/s,  $Z_0$  = 50  $\Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.



# **6 Detailed Description**

# 6.1 Functional Block Diagram



Pin numbers are for the DB, DW, and PW packages.

Figure 6-1. Logic diagram (positive logic)

#### **6.2 Device Functional Modes**

## **Function Table (Each Driver)**

	I	INPUTS <sup>(1)</sup>	,	OUTPUT	
DIN	FORCEON	FORCEOFF	VALID RIN RS-232 LEVEL	DOUT	DRIVER STATUS
Х	X	L	X	Z	Powered off
L	Н	Н	X	Н	Normal operation with
Н	Н	Н	X	L	auto-powerdown disabled
L	L	Н	Yes	Н	Normal operation with
Н	L	Н	Yes	L	auto-powerdown enabled
L	L	Н	No	Z	Powered off by
Н	L	Н	No	Z	auto-powerdown feature

(1) H = high level, L = low level, X = irrelevant, Z = high impedance

#### **Function Table (Each Receiver)**

	INPUTS <sup>(1)</sup>								
RIN	EN	VALID RIN RS-232 LEVEL	OUTPUT DOUT						
L	L	X	Н						
Н	L	X	L						
Х	Н	X	Z						
Open	L	No	н						

(1) H = high level, L = low level, X = irrelevant,

Z = high impedance (off),

Open = input disconnected or connected driver off

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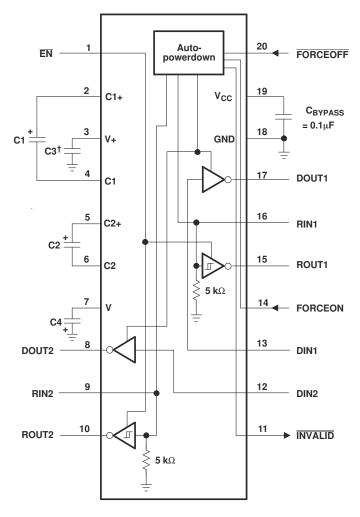


# 7 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

#### 7.1 Typical Application



 $^{\dagger}$  C3 can be connected to  $V_{CC}$  or GND.

NOTES: A. Resistor values shown are nominal.

B. Nonpolarized ceramic capacitors are acceptable. If polarized tantalum or electrolytic capacitors are used, they should be connected as shown.
 V<sub>CC</sub> vs CAPACITOR VALUES

V <sub>CC</sub>	C1	C2, C3, and C4
3.3 V $\pm$ 0.3 V	<b>0.1</b> μ <b>F</b>	<b>0.1</b> μF
5 V ± 0.5 V	<b>0.047</b> μ <b>F</b>	<b>0.33</b> μF
3 V to 5.5 V	<b>0.1</b> μ <b>F</b>	<b>0.47</b> μ <b>F</b>

Figure 7-1. Typical Operating Circuit and Capacitor Values



## 7.1.1 Detailed Design Procedure

MAX3223E has integrated charge-pump that generates positive and negative rails needed for RS-232 signal levels. Main design requirement is that charge-pump capacitor terminals must be connected with recommended capacitor values. Charge-pump rail voltages and device supply pin must be properly bypassed with ceramic capacitors

(1)

## 8 Device and Documentation Support

# 8.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### **8.2 Support Resources**

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 8.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

## 8.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## 8.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

#### 9 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Cł	anges from Revision A (September 2009) to Revision B (December 2023)	Page
•	Changed the numbering format for tables, figures, and cross-references throughout the document	1
•	Added the ESD Ratings tables	3
	Added the Thermal Information table	
•	Changed the I <sub>CC</sub> Auto-powerdown disabled max value from 1 mA to 1.3 mA in the Electrical Character	eristics 4
Cł	anges from Revision * (January 2006) to Revision A (September 2009)	Page
•	Deleted the RHL Pinout image	

## 10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



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#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
	. ,				_	. ,	(6)	(-)		( /	
MAX3223ECDW	LIFEBUY	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3223EC	
MAX3223ECDWR	LIFEBUY	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	0 to 70	MAX3223EC	
MAX3223EIDBR	ACTIVE	SSOP	DB	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP223EI	Samples
MAX3223EIDW	LIFEBUY	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3223EI	
MAX3223EIDWR	LIFEBUY	SOIC	DW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MAX3223EI	
MAX3223EIPWR	ACTIVE	TSSOP	PW	20	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	MP223EI	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# **PACKAGE OPTION ADDENDUM**

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continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

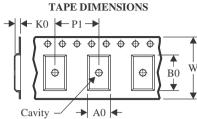


# PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





	· · · · · · · · · · · · · · · · · · ·
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
MAX3223ECDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
MAX3223EIDBR	SSOP	DB	20	2000	330.0	16.4	8.2	7.5	2.5	12.0	16.0	Q1
MAX3223EIDWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1
MAX3223EIPWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1



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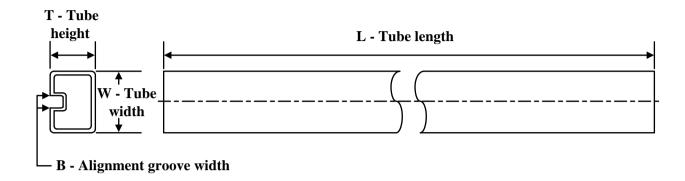
#### \*All dimensions are nominal

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
MAX3223ECDWR	SOIC	DW	20	2000	367.0	367.0	45.0
MAX3223EIDBR	SSOP	DB	20	2000	356.0	356.0	35.0
MAX3223EIDWR	SOIC	DW	20	2000	367.0	367.0	45.0
MAX3223EIPWR	TSSOP	PW	20	2000	356.0	356.0	35.0

# **PACKAGE MATERIALS INFORMATION**

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## **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
MAX3223ECDW	DW	SOIC	20	25	507	12.83	5080	6.6
MAX3223EIDW	DW	SOIC	20	25	507	12.83	5080	6.6





#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



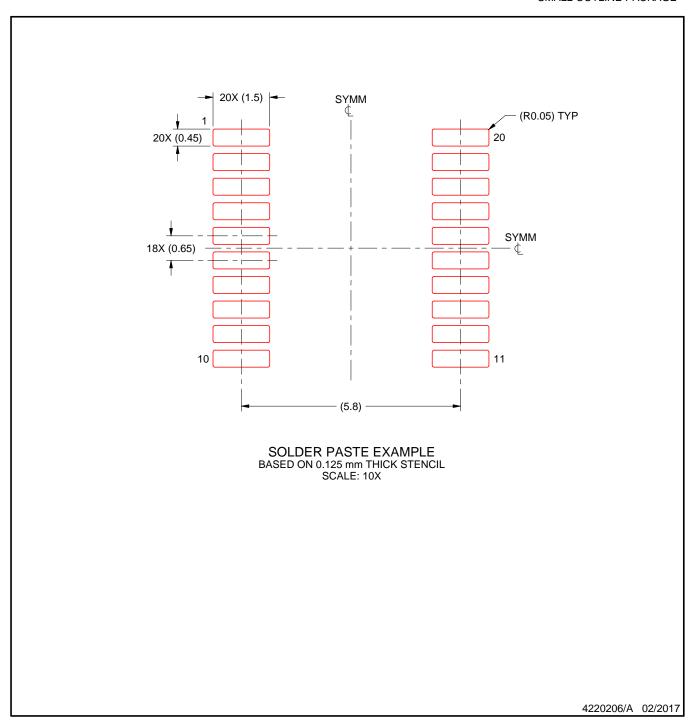


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





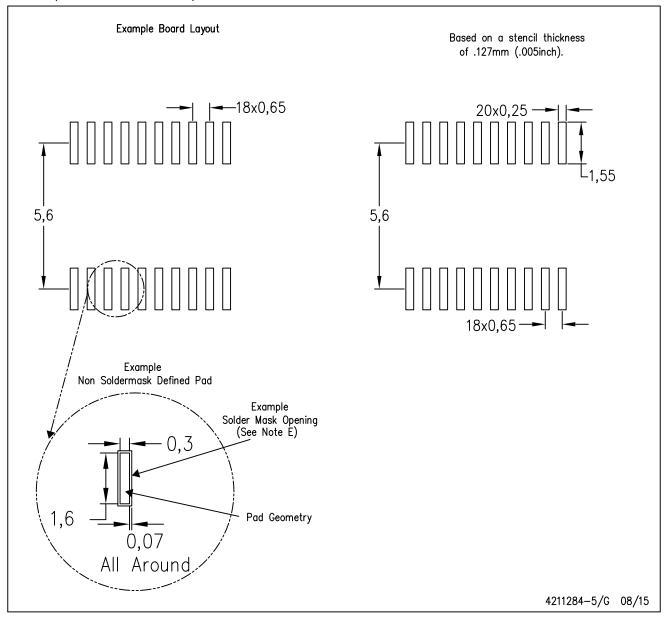
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



# PW (R-PDSO-G20)

# PLASTIC SMALL OUTLINE

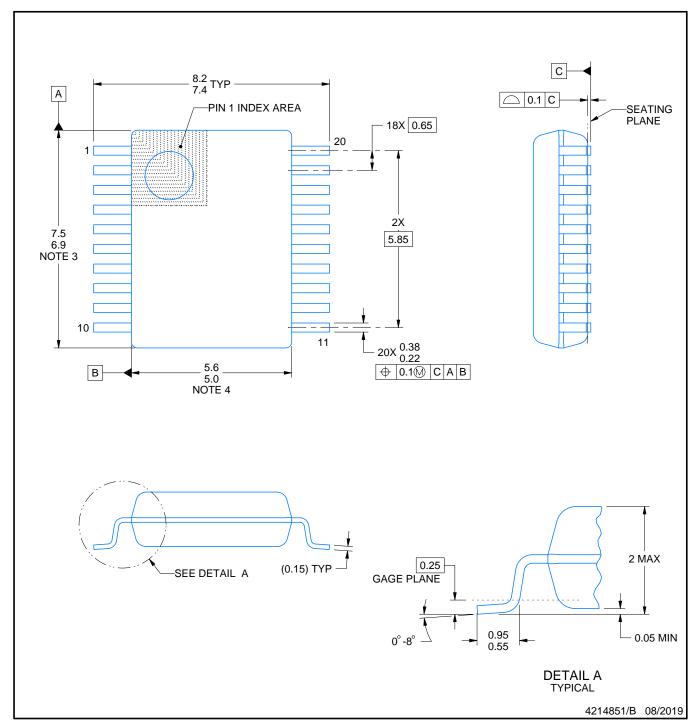


NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.







#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-150.



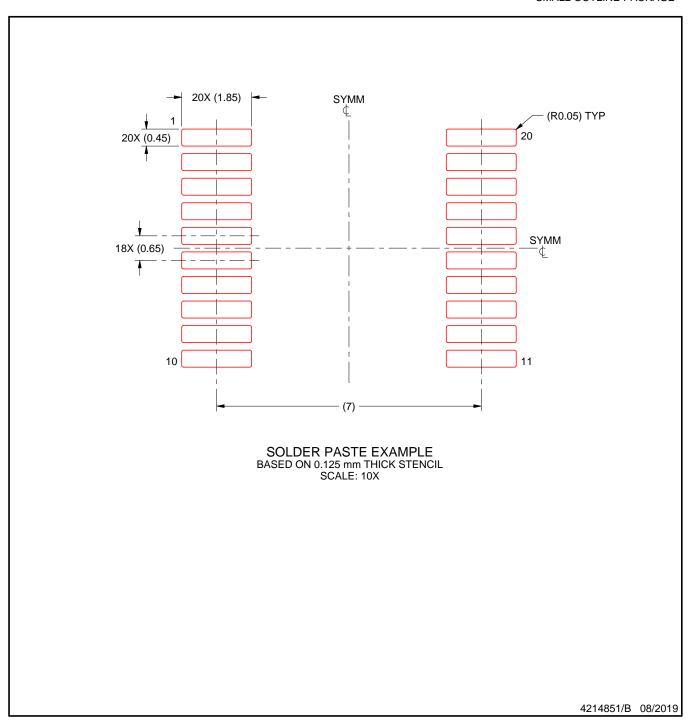


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





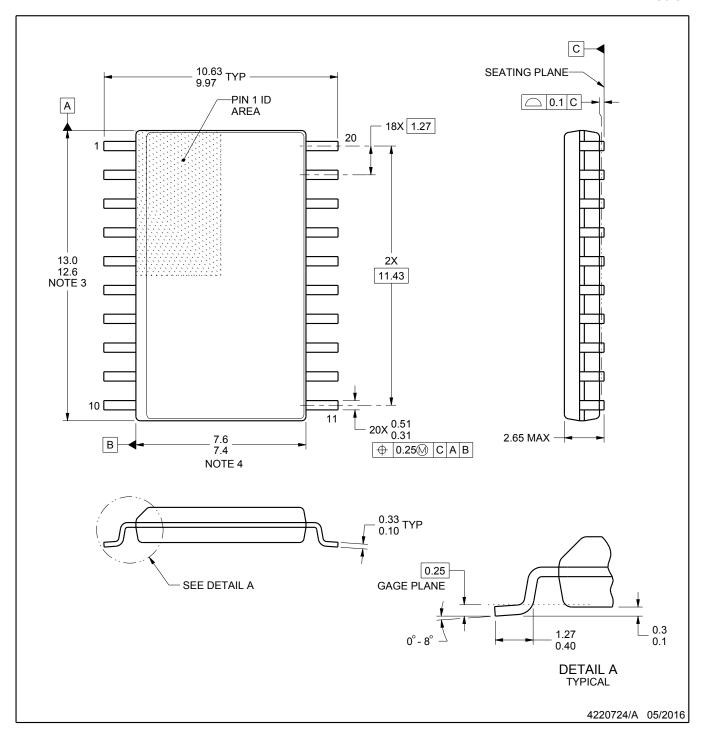
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





SOIC



#### NOTES:

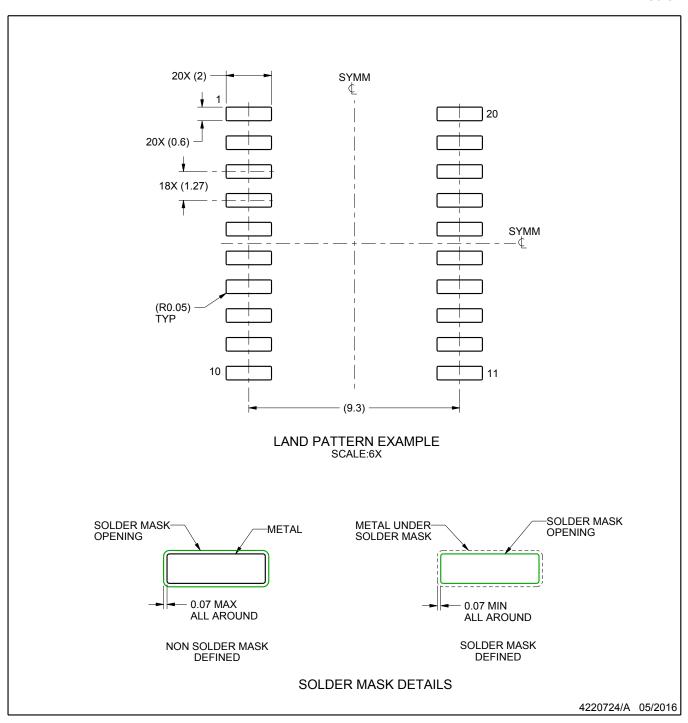
- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



SOIC

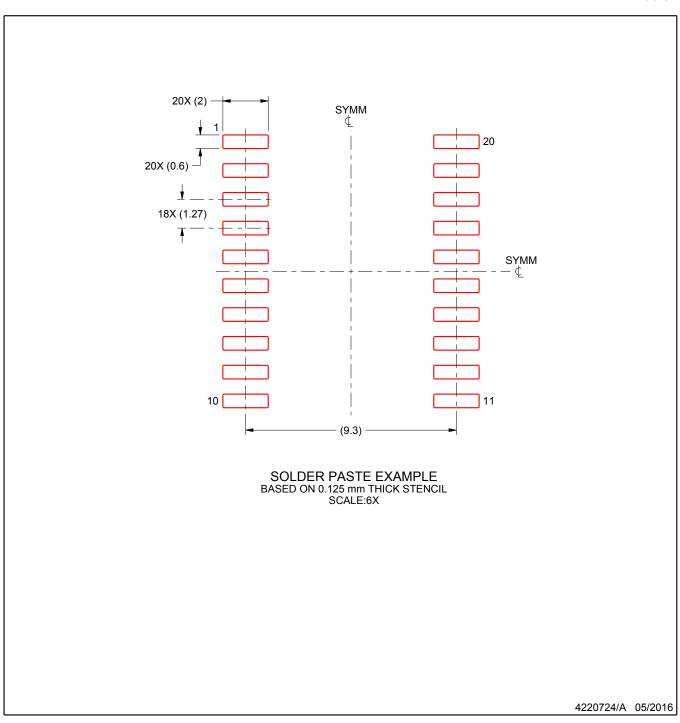


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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